

Product Summary

BV_{DSS}	R_{D(S)}(ON) Max	I_D Max T_C = +25°C
40V	7.3mΩ @ V _{GS} = 10V	70A
	9.8mΩ @ V _{GS} = 4.5V	44A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine-management systems
- Body control electronics
- DC-DC converters

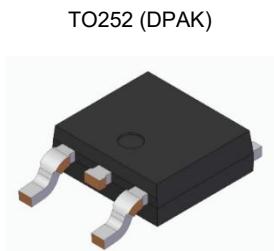
Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- High Conversion Efficiency
- Low R_{D(S)}(ON) – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMTH4007LK3Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

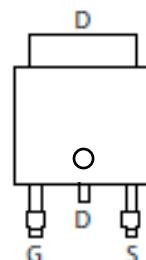
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

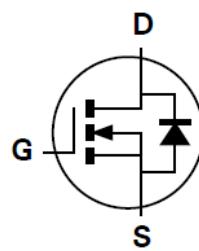
- Package: TO252
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.33 grams (Approximate)



Top View



Pinout Top View



Equivalent Circuit

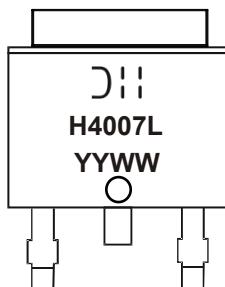
Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMTH4007LK3Q-13	TO252 (DPAK)	2500	Tape & Reel

Notes:

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



DMTH4007LK3Q

Document number: DS38158 Rev. 2 - 2

DII = Manufacturer's Marking
H4007L = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 26 = 2026)
WW = Week Code (01 to 53)

Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	40	V
Gate-Source Voltage	V_{GSS}	± 20	V
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 5)	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	16.8 13.9
Continuous Drain Current, $V_{GS} = 10\text{V}$ (Note 6)	$T_C = +25^\circ\text{C}$ $T_C = +100^\circ\text{C}$	I_D	70 51
Maximum Continuous Body Diode Forward Current (Note 6)	I_S	50	A
Pulsed Drain Current (10 μs Pulse, Duty Cycle = 1%)	I_{DM}	160	A
Avalanche Current, $L = 0.1\text{mH}$	I_{AS}	20	A
Avalanche Energy, $L = 0.1\text{mH}$	E_{AS}	20	mJ

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	2.6	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	47	$^\circ\text{C}/\text{W}$
Total Power Dissipation (Note 6)	P_D	59	W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	2.5	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	$V_{GS} = 0, I_D = 1\text{mA}$
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	$V_{DS} = 32\text{V}, V_{GS} = 0$
Gate-Source Leakage	I_{GSS}	—	—	± 100	nA	$V_{GS} = \pm 20\text{V}, V_{DS} = 0$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(\text{TH})}$	1	—	3	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(\text{ON})}$	—	5.5	7.3	$\text{m}\Omega$	$V_{GS} = 10\text{V}, I_D = 20\text{A}$
		—	8.6	9.8		$V_{GS} = 4.5\text{V}, I_D = 20\text{A}$
Diode Forward Voltage	V_{SD}	—	—	1.2	V	$V_{GS} = 0, I_S = 20\text{A}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	1895	—	pF	$V_{DS} = 30\text{V}, V_{GS} = 0, f = 1\text{MHz}$
Output Capacitance	C_{oss}	—	485	—		
Reverse Transfer Capacitance	C_{rss}	—	20.9	—	nC	$V_{DS} = 30\text{V}, I_D = 20\text{A}$
Gate Resistance	R_g	0.1	0.62	1.8		
Total Gate Charge ($V_{GS} = 4.5\text{V}$)	Q_g	—	12.4	—	nC	$V_{DS} = 0, V_{GS} = 0, f = 1\text{MHz}$
Total Gate Charge ($V_{GS} = 10\text{V}$)	Q_g	—	29.1	—		
Gate-Source Charge	Q_{gs}	—	5.9	—	ns	$V_{DD} = 30\text{V}, V_{GS} = 10\text{V}, I_D = 20\text{A}, R_g = 3\Omega$
Gate-Drain Charge	Q_{gd}	—	3.5	—		
Turn-On Delay Time	$t_{D(\text{ON})}$	—	5.4	—	ns	$I_F = 20\text{A}, dI/dt = 100\text{A}/\mu\text{s}$
Turn-On Rise Time	t_R	—	4.5	—		
Turn-Off Delay Time	$t_{D(\text{OFF})}$	—	16.2	—	ns	$I_F = 20\text{A}, dI/dt = 100\text{A}/\mu\text{s}$
Turn-Off Fall Time	t_F	—	3.5	—		
Body Diode Reverse-Recovery Time	t_{RR}	—	30.6	—	nC	$I_F = 20\text{A}, dI/dt = 100\text{A}/\mu\text{s}$
Body Diode Reverse-Recovery Charge	Q_{RR}	—	28.1	—		

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

6. Thermal resistance from junction to soldering point (on the exposed drain pad).

7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.

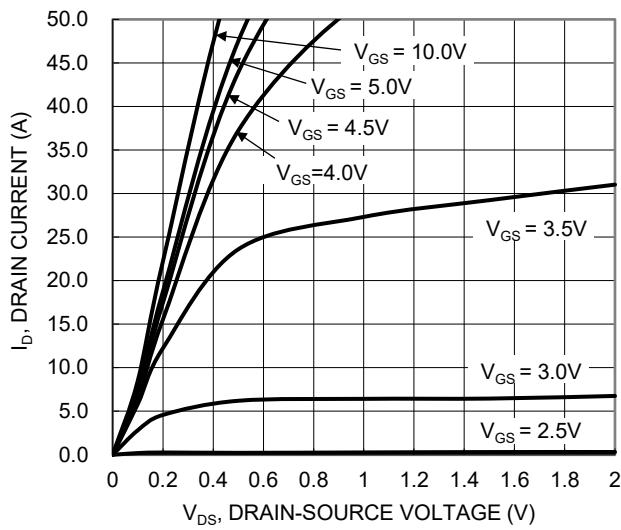


Figure 1. Typical Output Characteristic

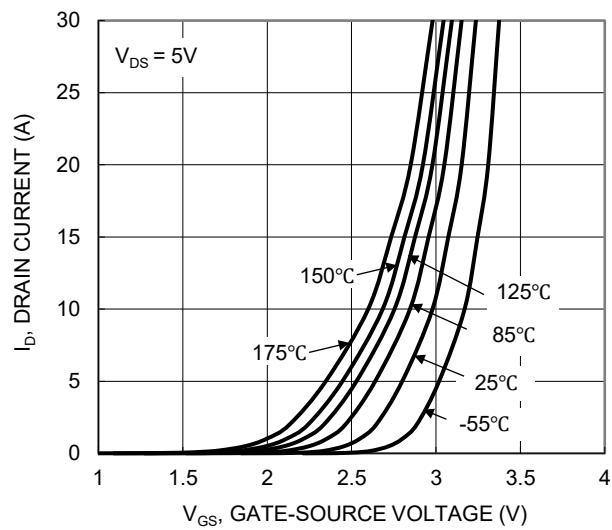


Figure 2. Typical Transfer Characteristic

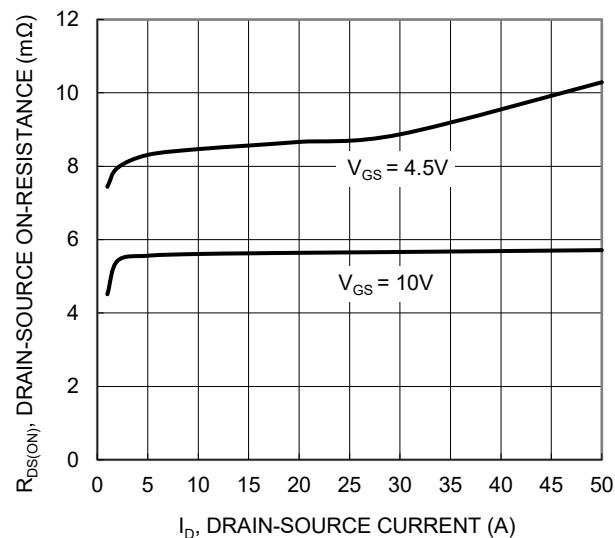


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

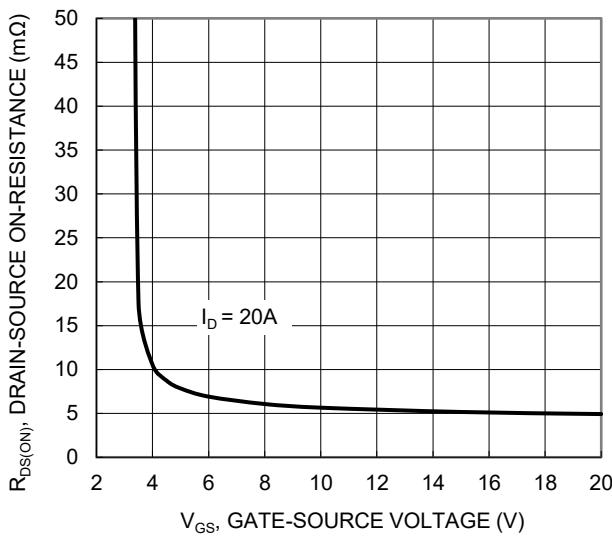


Figure 4. Typical Transfer Characteristic

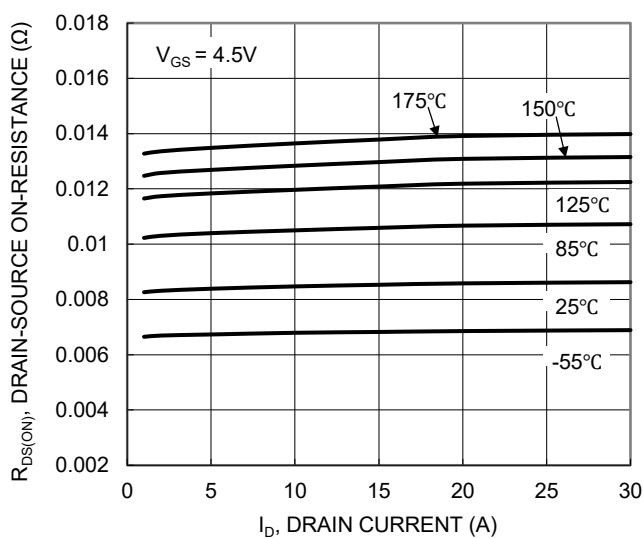


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

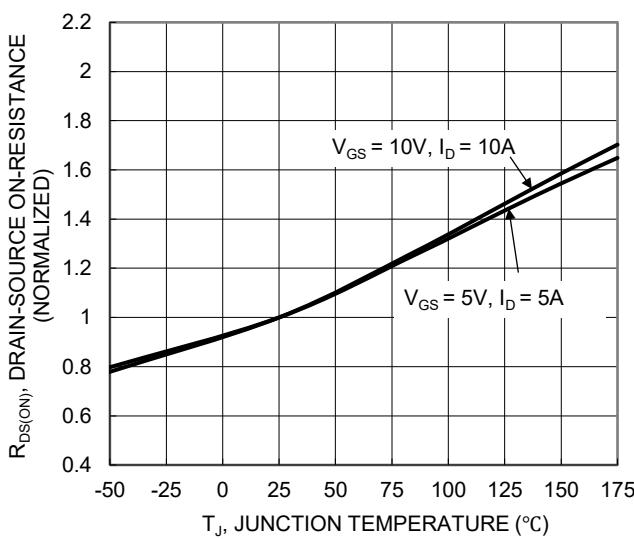
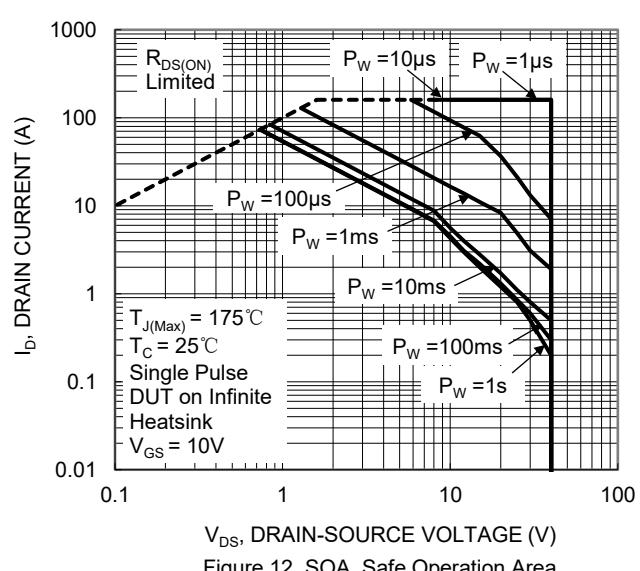
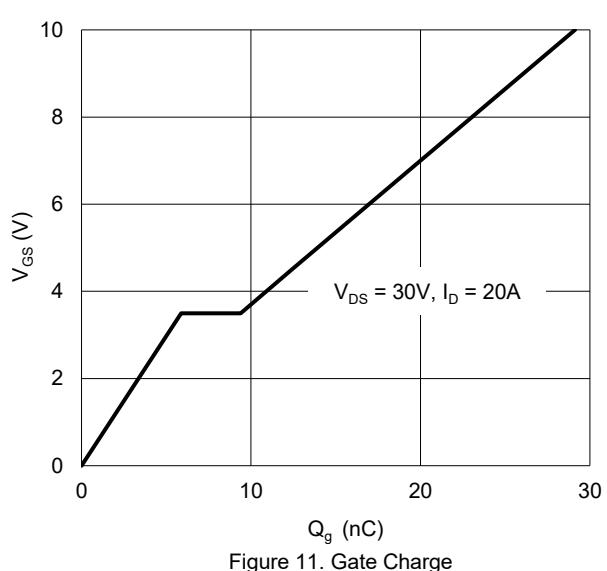
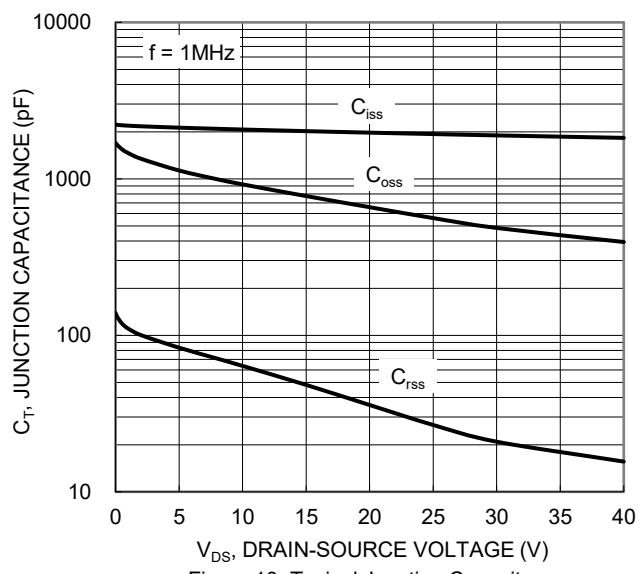
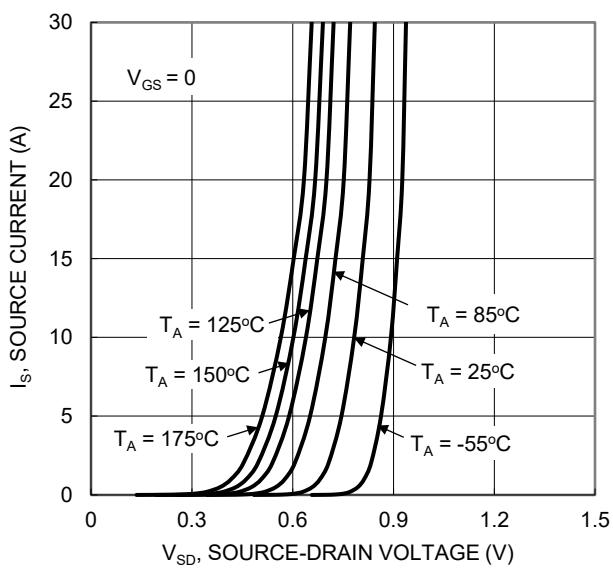
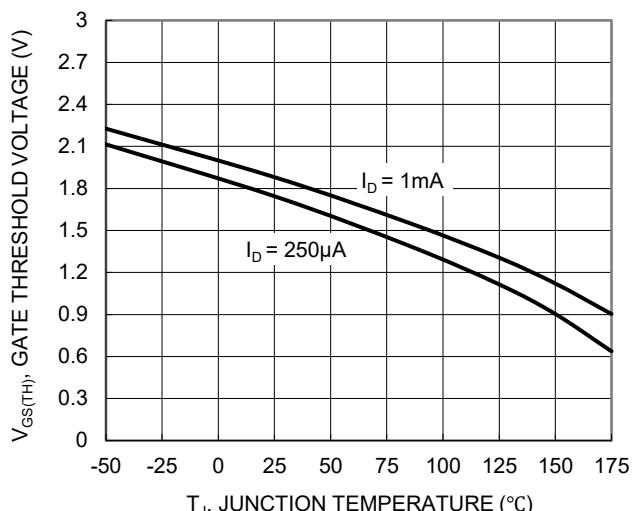
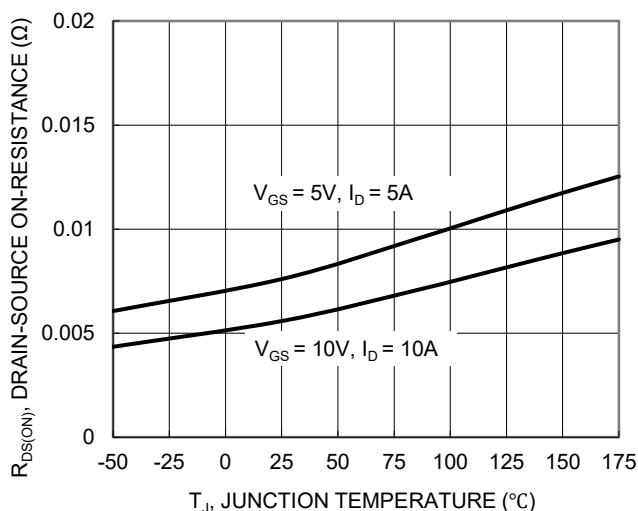


Figure 6. On-Resistance Variation with Temperature



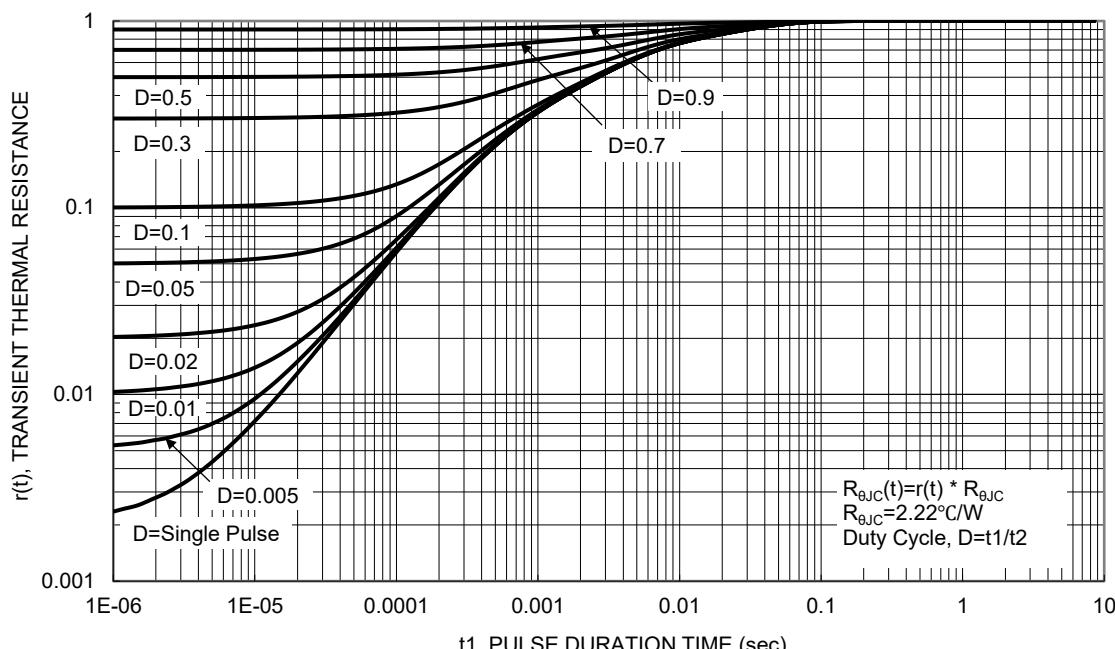
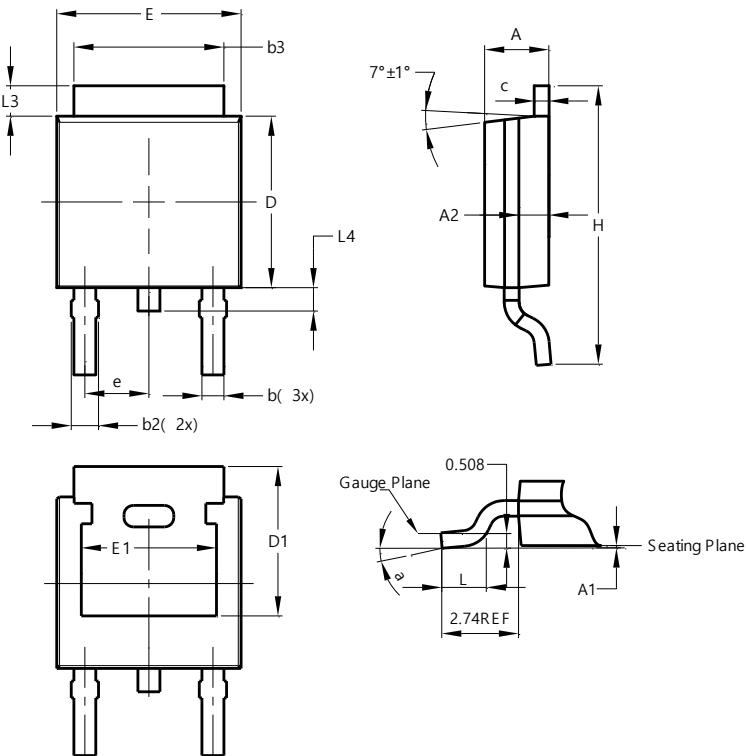


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



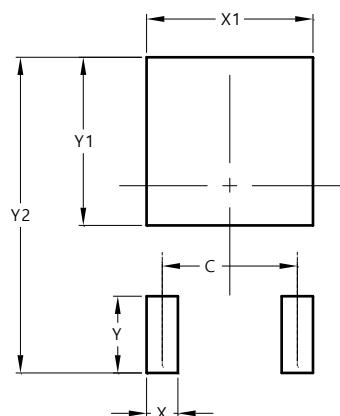
TO252 (DPAK)			
Dim	Min	Max	Typ
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.50	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	--	--
e	2.286 BSC		
E	6.45	6.70	6.58
E1	4.32	--	--
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	--

All Dimensions in mm

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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